

## Features

- High Power PIN Diode Switch  
(1 kW Max. Pw = 1 us, duty = 0.5%)
- DC Bias Voltage: +5.0 V, -15 V
- Typical Insertion Loss 2.0 dB
- Military Radar application
- Hermitical Sealing



## Electronical Specifications

Parameter	Specifications	Remarks
Frequency Range	8,500 MHz ~ 9,500 MHz	1,000 MHz
Insertion Loss (Max.)	2.5 dB Max.	
VSWR	1.8 : 1 Max.	
Isolation (Min.)	40.0 dB Min.	
Switching Time (Max.)	250 ns Max.	
DC Bias Current	5.0V@ 80mA -15.0V@ 10mA	
In/ Out Impedance	50 Ω	
Handling Power (Max.)	1 kW Max	Pw = 1 us, duty = 0.5%
Dimensions	31.75*31.75*7.6 mm	Excluding Connectors

## Environmental Specifications

Parameter	Specifications
Temperature	-54°C TO 95°C(OPERATING) -65°C TO 125°C(STORAGE)
Humidity	MIL-STD-202, METHOD 103B COND B
Shock	MIL-STD-202, METHOD 213, COND J
Vibration	MIL-STD-202, METHOD 214, COND A
Altitude	MIL-STD-202, METHOD 105C, COND B
Temperature Cycle	MIL-STD-202, METHOD107D, COND A

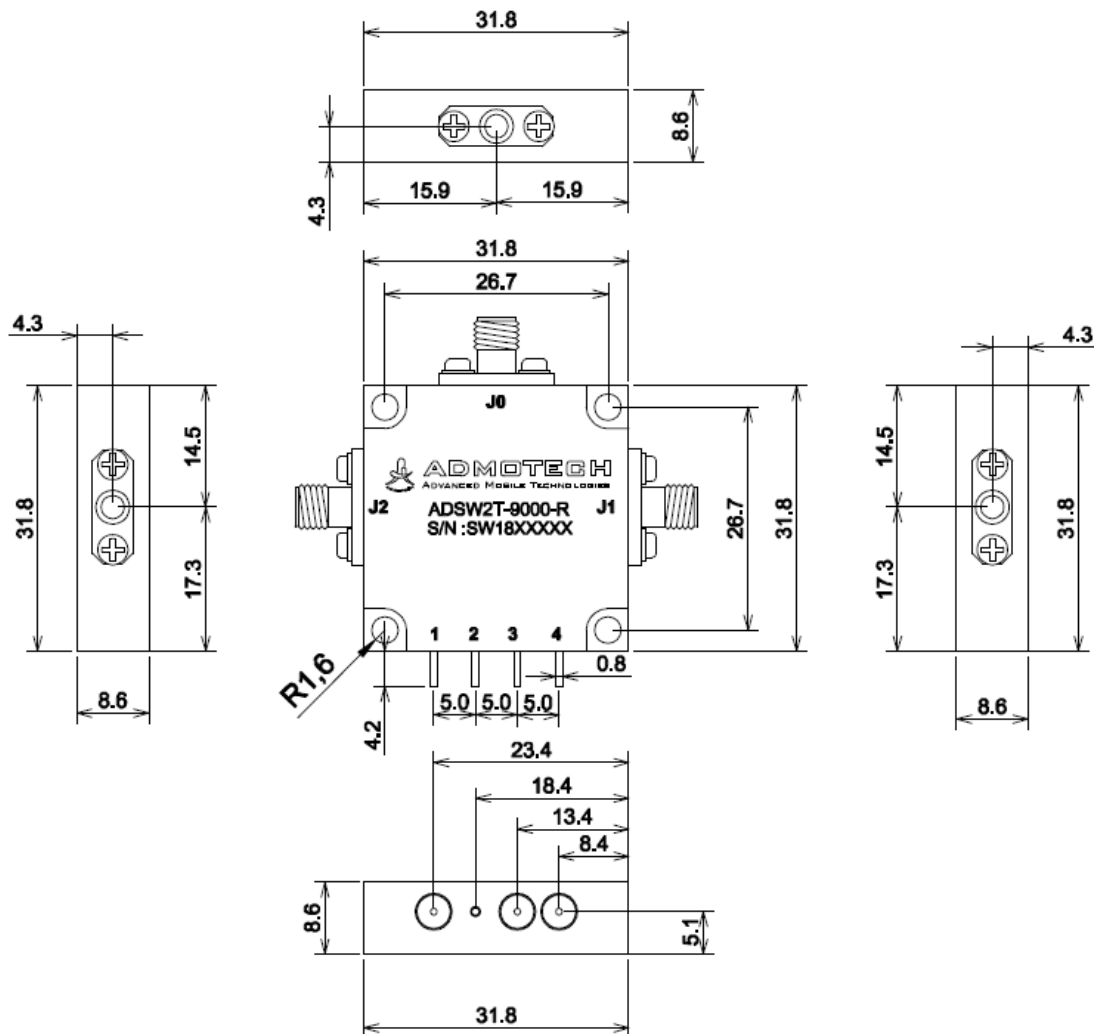
## Logic Control TTL

TTL	J0-J1	J0-J2
Low	Insertion Loss	Isolation
High	Isolation	Insertion Loss

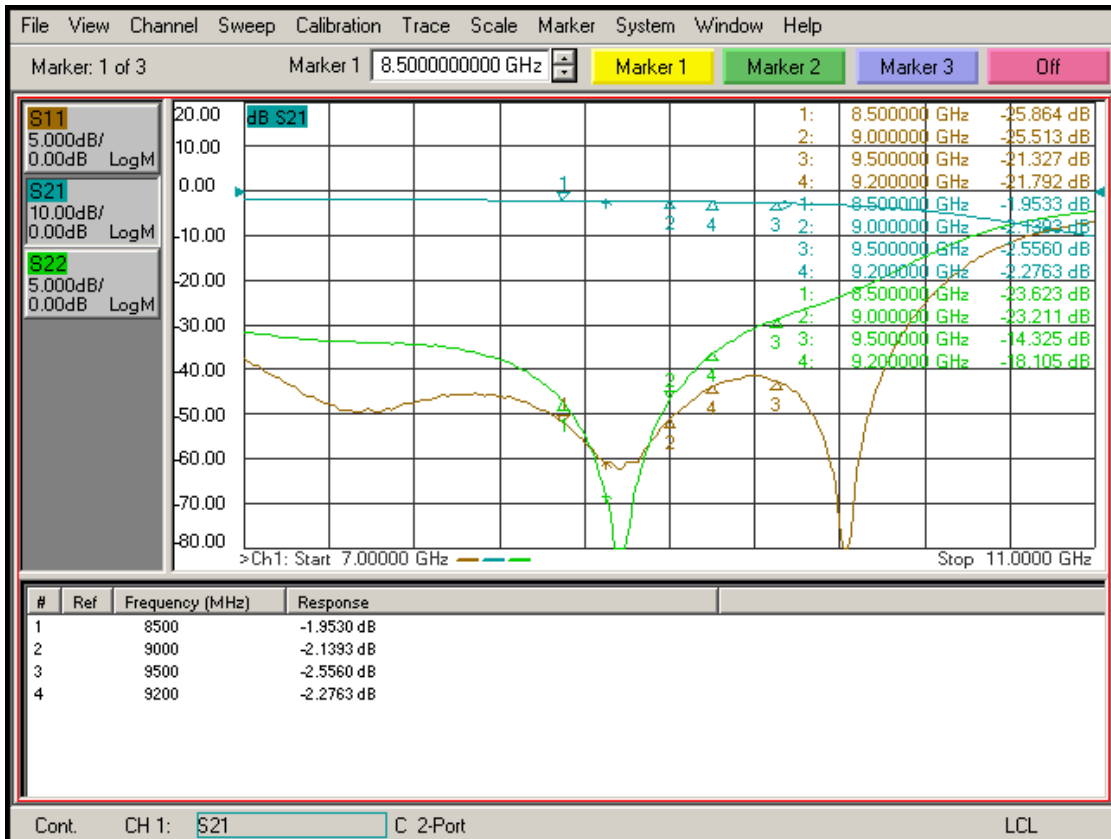
## PIN Map

PIN.1	PIN.2	PIN.3	PIN.4
TTL	GND	-15.0V	5.0V

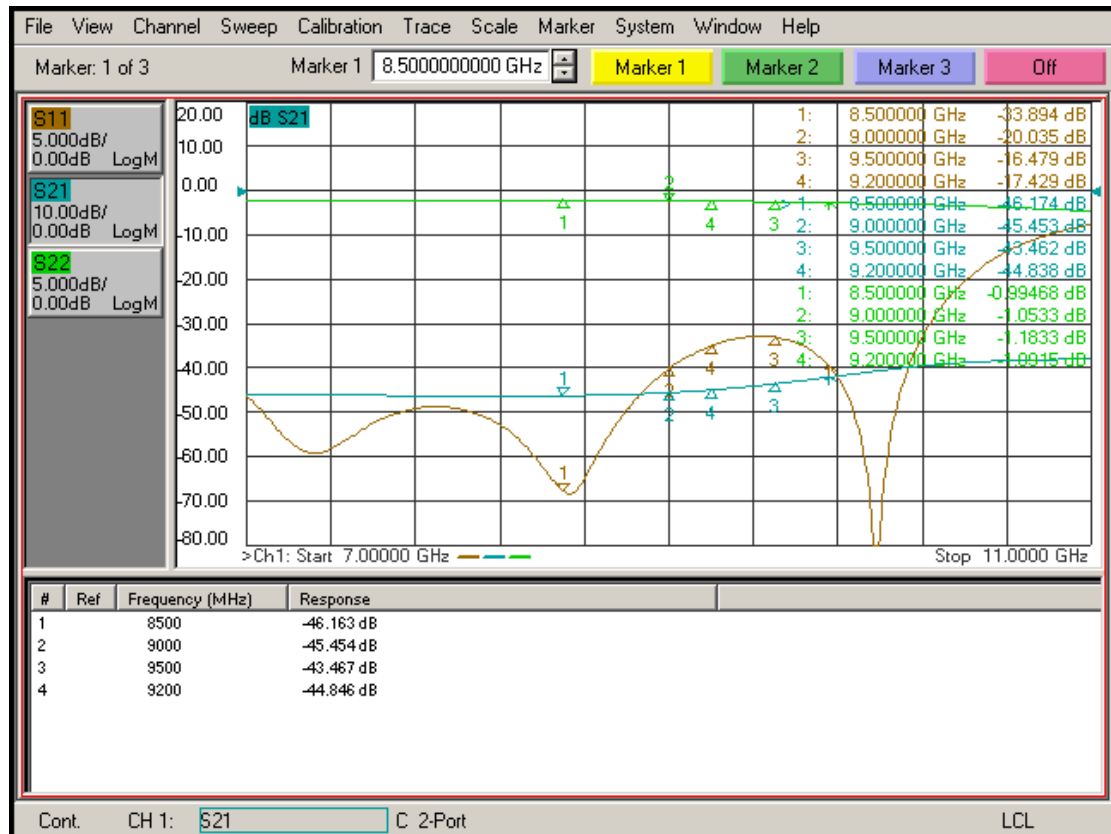
## Outline drawing (Unit: mm)



## Typical S-parameter Response



[J0-J1 Transmission]



[J0-J2 Isolation]

## Switching Time



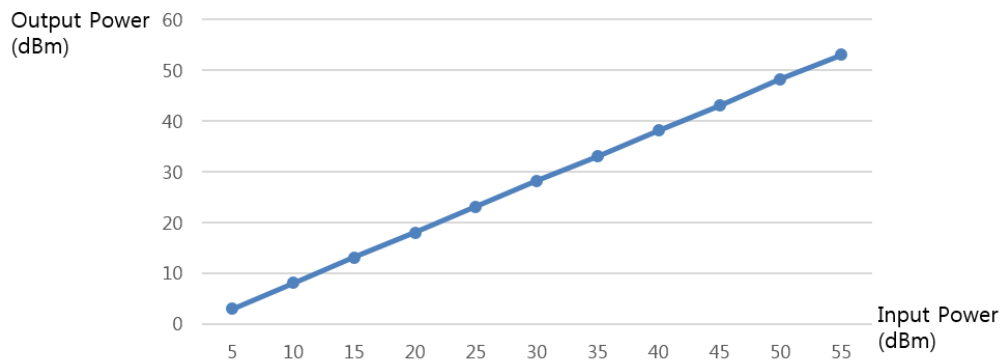
[Switching ON Time: 250ns]



[Switching OFF Time: 250ns]

## High Power Test

### Input Power vs Output Power



Test performed @ 9.2GHz